

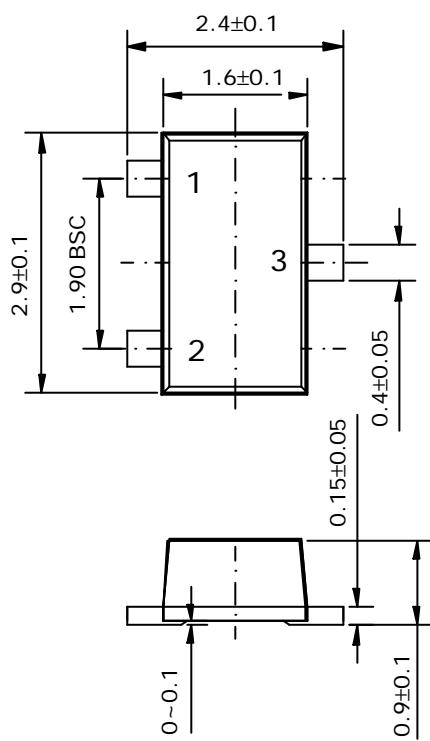
Features

- Extremely low collector-to-emitter saturation voltage ($V_{CE(SAT)} = 0.15V$ Typ. @ $I_C/I_B = 400mA/20mA$)
- Suitable for low voltage large current drivers
- Complementary pair with DP100S
- Switching Application

Ordering Information

Type NO.	Marking	Package Code
DN100S	N03	SOT-23F

Outline Dimensions

unit : mm


PIN Connections
1. Base
2. Emitter
3. Collector

Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V _{CBO}	15	V
Collector-Emitter voltage	V _{CEO}	12	V
Emitter-Base voltage	V _{EBO}	5	V
Collector current	I _C	1	A
Collector dissipation	P _C	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~150	°C

Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	BV _{CBO}	I _C =50μA, I _E =0	15	-	-	V
Collector-Emitter breakdown voltage	BV _{CEO}	I _C =1mA, I _B =0	12	-	-	V
Emitter-Base breakdown voltage	BV _{EBO}	I _E =50μA, I _C =0	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} =12V, I _E =0	-	-	0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0	-	-	0.1	μA
DC current gain	h _{FE1}	V _{CE} =1V, I _C =100mA	200	-	450	-
	h _{FE2}	V _{CE} =1V, I _C =1A	70	-	-	-
Collector-Emitter saturation voltage	V _{CE(sat)}	I _C =400mA, I _B =20mA	-	-	0.25	V
Base-Emitter saturation voltage	V _{BE(sat)}	I _C =400mA, I _B =20mA	-	-	1.2	V
Transition frequency	f _T	V _{CE} =5V, I _C =50mA	-	260	-	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	5	-	pF

Electrical Characteristic Curves

Fig. 1 P_C - T_a

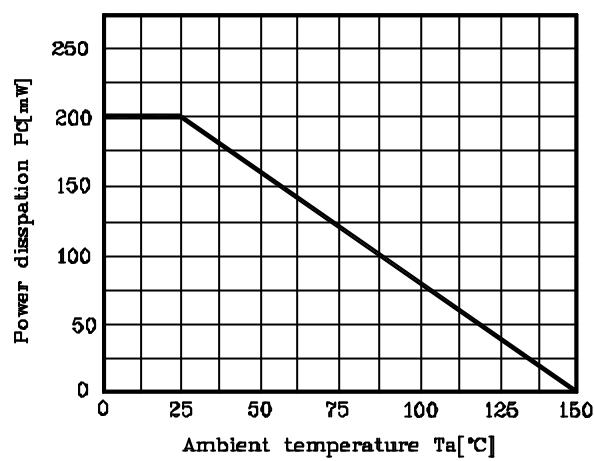


Fig. 2 I_C - V_{BE}

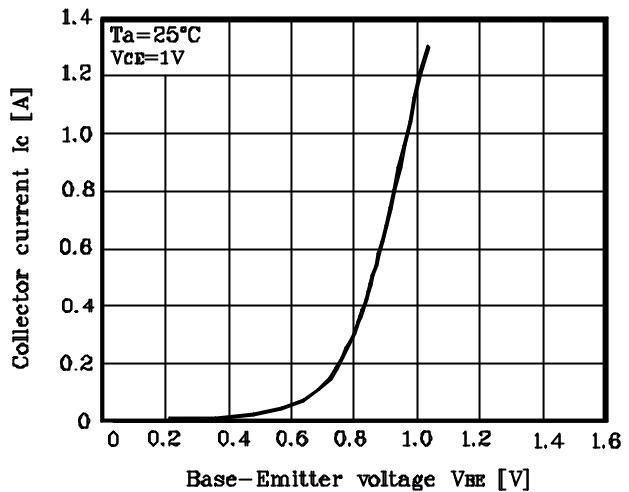


Fig. 3 h_{FE} - I_C

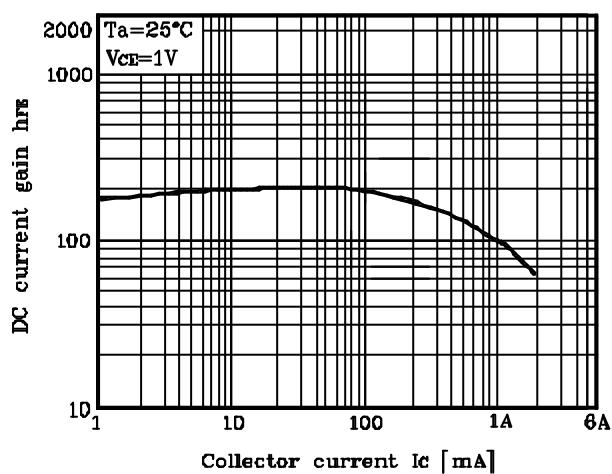


Fig. 4 $V_{CE(sat)}$ - I_C

